Switch-mode Schottky Power Rectifier

Surface Mount Power Package

MBRD5H100, NBRD5H100

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 0.4 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
 - Machine Model = C (> 400 V)
 - Human Body Model = 3B (> 8000 V)



ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 5 AMPERES, 100 VOLTS



DPAK CASE 369C



(Pin 1: No Connect)

MARKING DIAGRAM



A = Assembly Location

Y = Year
WW = Work Week
B5100 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRD5H100T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NBRD5H100T4G	DPAK (Pb-Free)	2,500 / Tape & Reel
NBRD5H100T4G-VF01	DPAK (Pb-Free)	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBRD5H100, NBRD5H100

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current T _C = 171°C	I _{F(AV)}	5	Α
Peak Repetitive Forward Current (Square Wave, Duty = 0.5) T _C = 171°C	IFRM	10	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	105	Α
Operating Junction and Storage Temperature Range (Note 1)	T _J , T _{stg}	-65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case (Note 2) Junction-to-Ambient (Note 2)	R _{θJC} R _{θJA}	1.6 95.8	°C/W

^{2.} When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) ($I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C}$) ($I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C}$)	V _F	0.71 0.60	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T _J = 125°C) (Rated dc Voltage, T _J = 25°C)	I _R	4.5 3.5	mA μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

MBRD5H100, NBRD5H100

TYPICAL CHARACTERISTICS

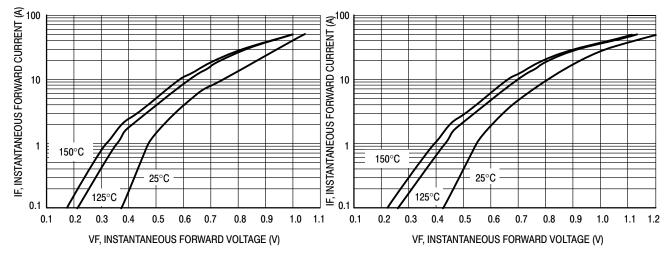


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

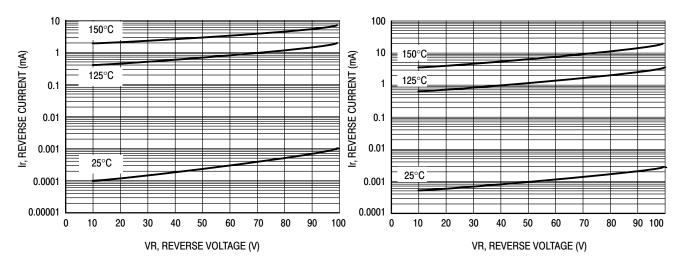


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

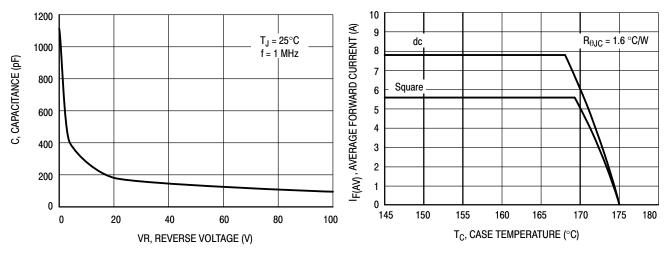
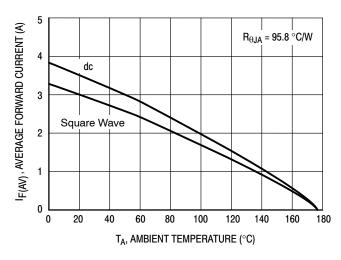


Figure 5. Typical Capacitance

Figure 6. Current Derating, Case

MBRD5H100, NBRD5H100

TYPICAL CHARACTERISTICS



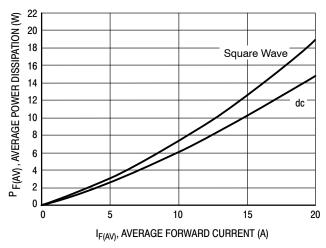


Figure 7. Current Derating, Ambient

Figure 8. Forward Power Dissipation

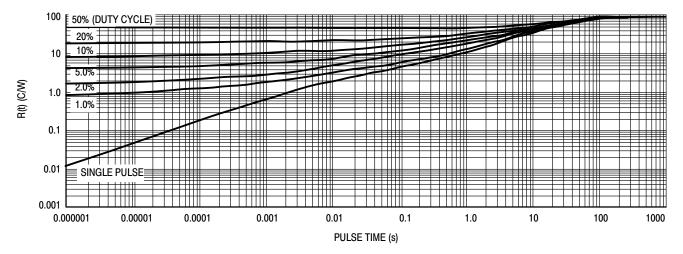
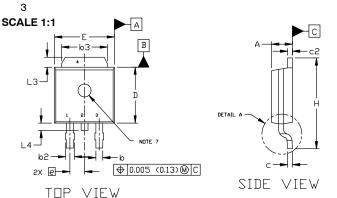


Figure 9. Thermal Response, Junction-to-Case

DPAK (SINGLE GAUGE)

CASE 369C **ISSUE G**

DATE 31 MAY 2023

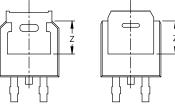


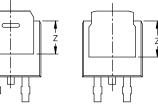


- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE DUTERMOST EXTREMES OF THE PLASTIC BODY.

 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
MIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
ھ	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b 3	0.180	0.215	4.57	5.46
Ū	0.018	0.024	0.46	0.61
5	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29 BSC	
Η	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 B2C		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040	-	1.01
Z	0.155		3.93	

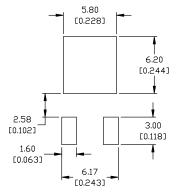


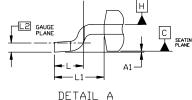


BOTTOM VIEW

BOTTOM VIEW

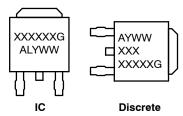
ALTERNATE CONSTRUCTIONS





CW ROTATED 90°

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT* *FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

S

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
COLLECTOR	DRAIN	CATHODE	2. ANODE	ANODE
EMITTER	SOURCE	ANODE	3. GATE	CATHODE
COLLECTOR	4. DRAIN	CATHODE	ANODE	ANODE

STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE 3 FMITTER 3 RESISTOR ADJUST 3 GATE 4. COLLECTOR 4. CATHODE 4. ANODE 4. CATHODE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales